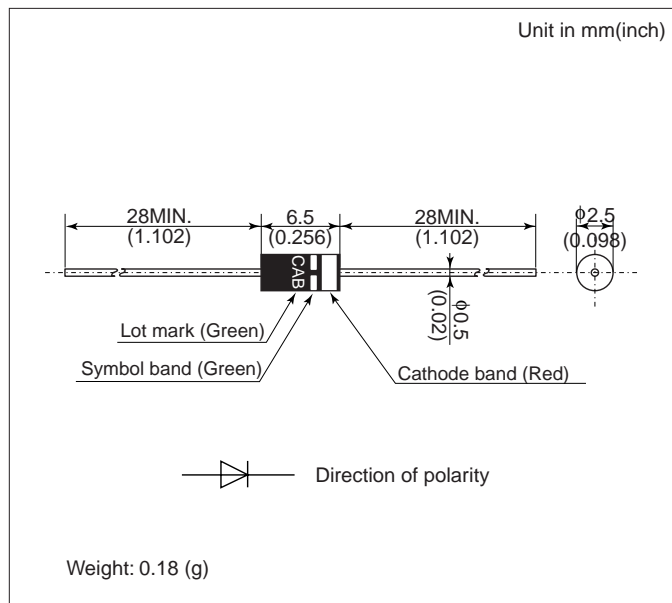


DHM3UF80

FEATURES

- For high resolution displays and TV receivers.
- Diffused-junction.
- Excellent high temperature output characteristics
(Small leakage current at high temperature
and excellent reverse characteristics)

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

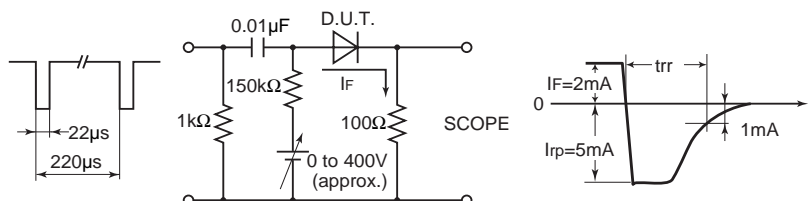
Item	Type		DHM3UF80
Repetitive Peak Reverse Voltage*	V_{RRM}	kV	8
Non-Repetitive Peak Reverse Voltage*	V_{RSM}	kV	10
Average Forward Current	$I_{F(AV)}$	mA	1 (100 kHz C-Load)
			3 (15.75kHz C-Load)
Surge(Non-Repetitive) Forward Current	I_{FSM}	A	0.5
Operating Junction Temperature	T_j	°C	-40 ~ +120
Storage Temperature	T_{stg}	°C	-40 ~ +120

CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Item	Symbols	Units	Min.	Typ.	Max.	Test Conditions
Peak Reverse Current*	I_{RRM}	μA	—	—	2.0	$V_R = V_{RRM}$
Peak Forward Voltage	V_{FM}	V	—	—	23	$I_{FM} = 5\text{mA}$
Reverse Recovery Time	t_{rr}	ns	—	—	40	$I_F = 2\text{mA}$, $I_{RP} = 5\text{mA}$, 1mA recovery

Notes *Diode tested in adequate thermal and dielectric medium.

Reverse recovery time (t_{rr}) test circuit



HITACHI POWER SEMICONDUCTORS

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